

TC7660

1.0 ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings*

Supply Voltage	+10.5V
LV and OSC Inputs Voltage: (Note 1)	
.....	-0.3V to V_{SS} for $V^+ < 5.5V$
.....	$(V^+ - 5.5V)$ to (V^+) for $V^+ > 5.5V$
Current into LV	20 μA for $V^+ > 3.5V$
Output Short Duration ($V_{SUPPLY} \leq 5.5V$).....	Continuous
Package Power Dissipation: ($T_A \leq 70^\circ C$)	
8-Pin Cerdip	800 mW
8-Pin PDIP	730 mW
8-Pin SOIC	470 mW
Operating Temperature Range:	
C Suffix	$0^\circ C$ to $+70^\circ C$
I Suffix	$-25^\circ C$ to $+85^\circ C$
E Suffix	$-40^\circ C$ to $+85^\circ C$
M Suffix	$-55^\circ C$ to $+125^\circ C$
Storage Temperature Range	$-65^\circ C$ to $+160^\circ C$
ESD protection on all pins (HBM)	≥ 3 kV
Maximum Junction Temperature	$150^\circ C$

* **Notice:** Stresses above those listed under "Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operational sections of this specification is not intended. Exposure to maximum rating conditions for extended periods may affect device reliability.

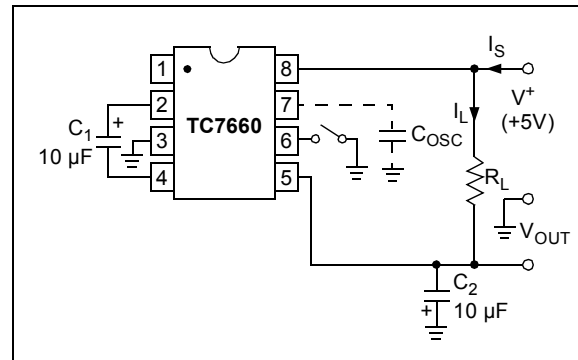


FIGURE 1-1: TC7660 Test Circuit.

ELECTRICAL SPECIFICATIONS

Electrical Characteristics: Unless otherwise noted, specifications measured over operating temperature range with $V^+ = 5V$, $C_{OSC} = 0$, refer to test circuit in Figure 1-1.

Parameters	Sym	Min	Typ	Max	Units	Conditions
Supply Current	I^+	—	80	180	μA	$R_L = \infty$
Supply Voltage Range, High	V^+_{H}	3.0	—	10	V	$\text{Min} \leq T_A \leq \text{Max}$, $R_L = 10$ k Ω , LV Open
Supply Voltage Range, Low	V^+_{L}	1.5	—	3.5	V	$\text{Min} \leq T_A \leq \text{Max}$, $R_L = 10$ k Ω , LV to GND
Output Source Resistance	R_{OUT}	—	70	100	Ω	$I_{OUT}=20$ mA, $T_A = +25^\circ C$
		—	—	120		$I_{OUT}=20$ mA, $T_A \leq +70^\circ C$ (C Device)
		—	—	130		$I_{OUT}=20$ mA, $T_A \leq +85^\circ C$ (E and I Device)
		—	104	150		$I_{OUT}=20$ mA, $T_A \leq +125^\circ C$ (M Device)
		—	150	300		$V^+ = 2V$, $I_{OUT} = 3$ mA, LV to GND $0^\circ C \leq T_A \leq +70^\circ C$
		—	160	600		$V^+ = 2V$, $I_{OUT} = 3$ mA, LV to GND $-55^\circ C \leq T_A \leq +125^\circ C$ (M Device)
Oscillator Frequency	f_{OSC}	—	10	—	kHz	Pin 7 open
Power Efficiency	P_{EFF}	95	98	—	%	$R_L = 5$ k Ω
Voltage Conversion Efficiency	V_{OUTEFF}	97	99.9	—	%	$R_L = \infty$
Oscillator Impedance	Z_{OSC}	—	1.0	—	M Ω	$V^+ = 2V$
		—	100	—	k Ω	$V^+ = 5V$

Note 1: Destructive latch-up may occur if voltages greater than V^+ or less than GND are supplied to any input pin.

2.0 TYPICAL PERFORMANCE CURVES

Note: The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only. The performance characteristics listed herein are not tested or guaranteed. In some graphs or tables, the data presented may be outside the specified operating range (e.g., outside specified power supply range) and therefore outside the warranted range.

Note: Unless otherwise indicated, $C_1 = C_2 = 10 \mu\text{F}$, $\text{ESR}_{C1} = \text{ESR}_{C2} = 1 \Omega$, $T_A = 25^\circ\text{C}$. See Figure 1-1.

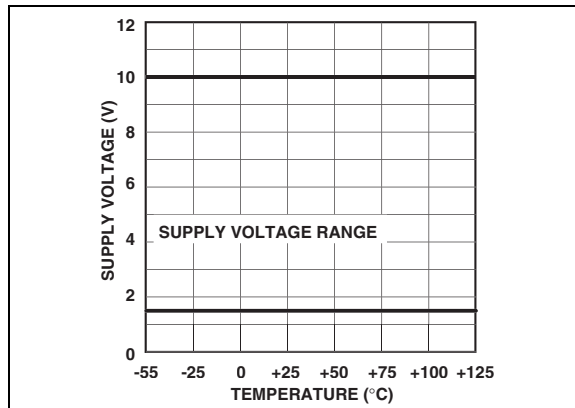


FIGURE 2-1: Operating Voltage vs. Temperature.

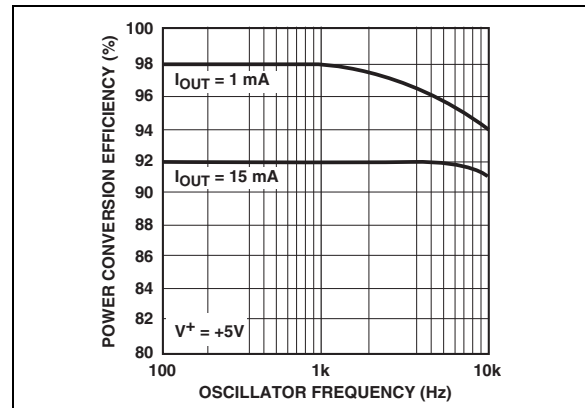


FIGURE 2-4: Power Conversion Efficiency vs. Oscillator Frequency.

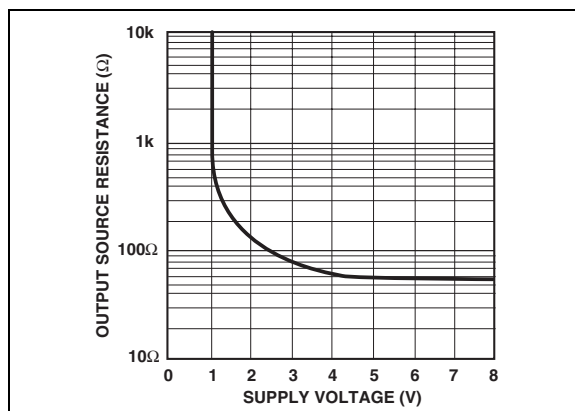


FIGURE 2-2: Output Source Resistance vs. Supply Voltage.

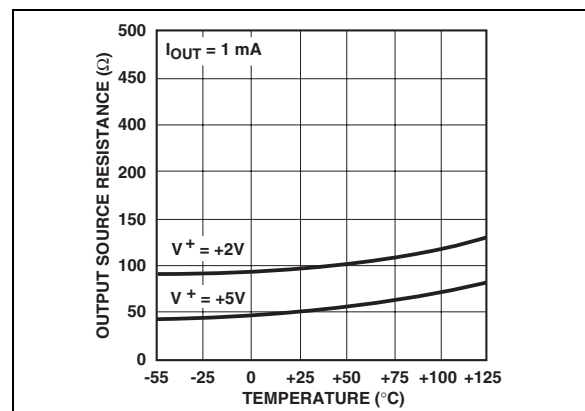


FIGURE 2-5: Output Source Resistance vs. Temperature.

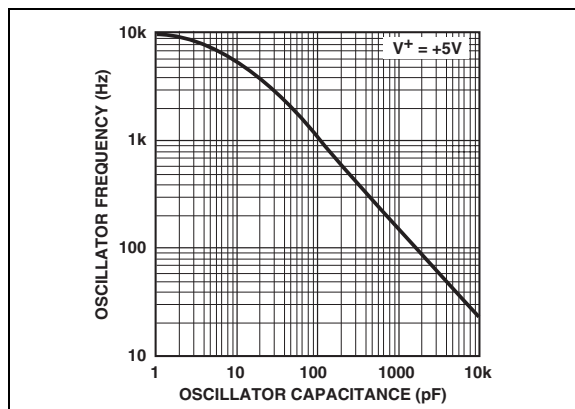


FIGURE 2-3: Frequency of Oscillation vs. Oscillator Capacitance.

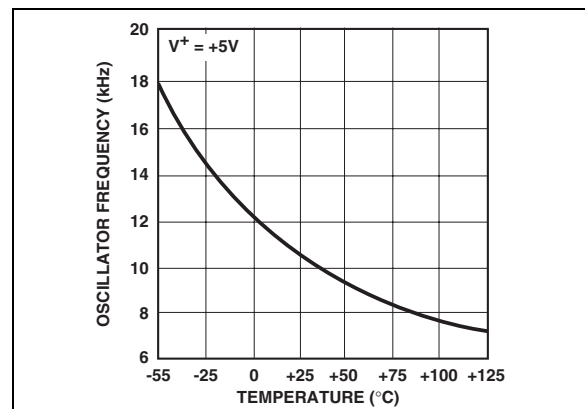


FIGURE 2-6: Unloaded Oscillator Frequency vs. Temperature.

TC7660

Note: Unless otherwise indicated, $C_1 = C_2 = 10 \mu\text{F}$, $\text{ESR}_{C1} = \text{ESR}_{C2} = 1 \Omega$, $T_A = 25^\circ\text{C}$. See Figure 1-1.

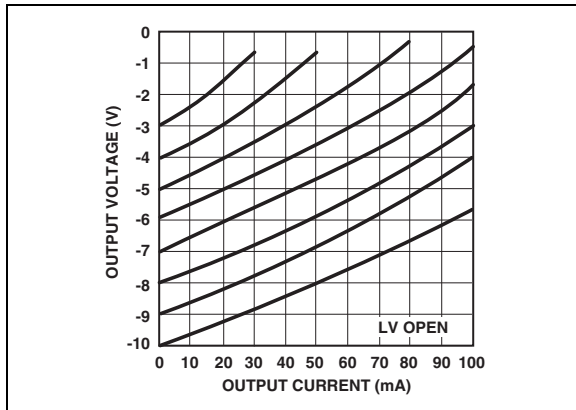


FIGURE 2-7: Output Voltage vs. Output Current.

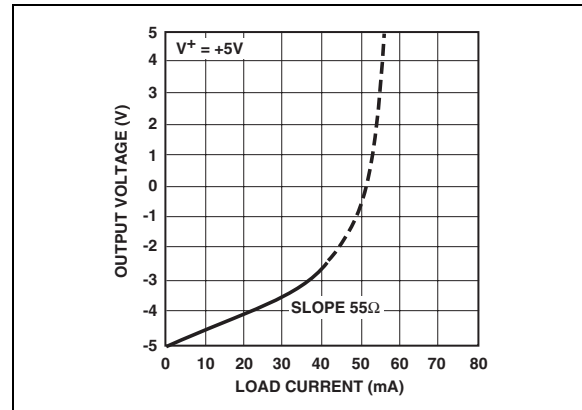


FIGURE 2-10: Output Voltage vs. Load Current.

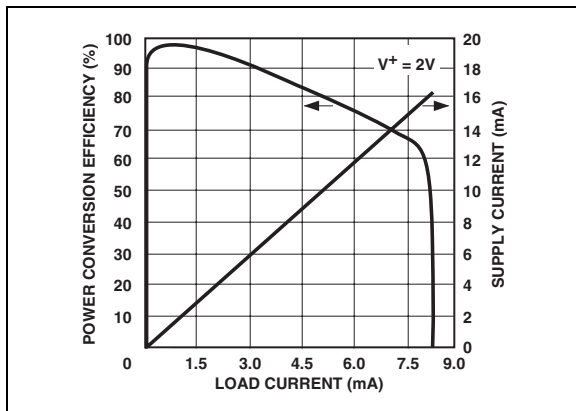


FIGURE 2-8: Supply Current and Power Conversion Efficiency vs. Load Current.

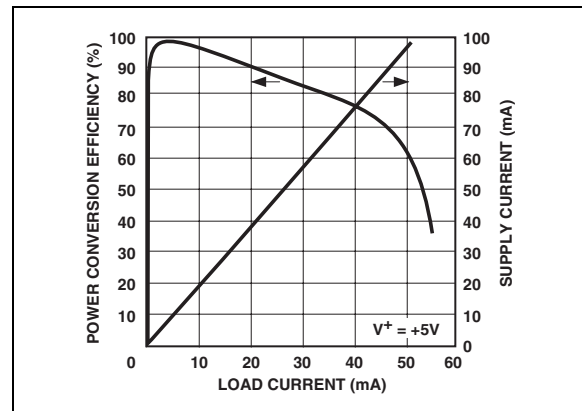


FIGURE 2-11: Supply Current and Power Conversion Efficiency vs. Load Current.

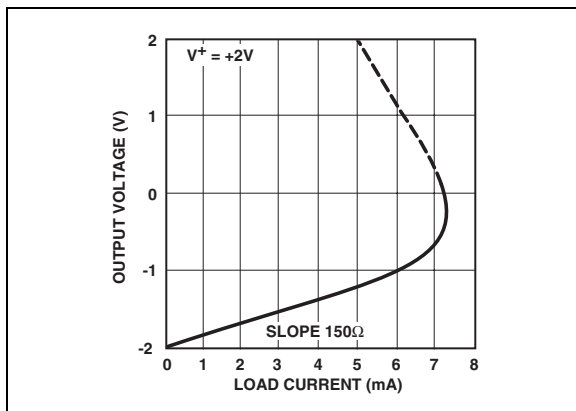


FIGURE 2-9: Output Voltage vs. Load Current.

3.0 PIN DESCRIPTIONS

The descriptions of the pins are listed in Table 3-1.

TABLE 3-1: PIN FUNCTION TABLE

Pin No.	Symbol	Description
1	NC	No connection
2	CAP ⁺	Charge pump capacitor positive terminal
3	GND	Ground terminal
4	CAP ⁻	Charge pump capacitor negative terminal
5	V _{OUT}	Output voltage
6	LV	Low voltage pin. Connect to GND for V ₊ < 3.5V
7	OSC	Oscillator control input. Bypass with an external capacitor to slow the oscillator
8	V ⁺	Power supply positive voltage input

3.1 Charge Pump Capacitor (CAP⁺)

Positive connection for the charge pump capacitor, or flying capacitor, used to transfer charge from the input source to the output. In the voltage-inverting configuration, the charge pump capacitor is charged to the input voltage during the first half of the switching cycle. During the second half of the switching cycle, the charge pump capacitor is inverted and charge is transferred to the output capacitor and load.

It is recommended that a low ESR (equivalent series resistance) capacitor be used. Additionally, larger values will lower the output resistance.

3.2 Ground (GND)

Input and output zero volt reference.

3.3 Charge Pump Capacitor (CAP⁻)

Negative connection for the charge pump capacitor, or flying capacitor, used to transfer charge from the input to the output. Proper orientation is imperative when using a polarized capacitor.

3.4 Output Voltage (V_{OUT})

Negative connection for the charge pump output capacitor. In the voltage-inverting configuration, the charge pump output capacitor supplies the output load during the first half of the switching cycle. During the second half of the switching cycle, charge is restored to the charge pump output capacitor.

It is recommended that a low ESR (equivalent series resistance) capacitor be used. Additionally, larger values will lower the output ripple.

3.5 Low Voltage Pin (LV)

The low voltage pin ensures proper operation of the internal oscillator for input voltages below 3.5V. The low voltage pin should be connected to ground (GND) for input voltages below 3.5V. Otherwise, the low voltage pin should be allowed to float.

3.6 Oscillator Control Input (OSC)

The oscillator control input can be utilized to slow down or speed up the operation of the TC7660. Refer to Section 5.4, "Changing the TC7660 Oscillator Frequency", for details on altering the oscillator frequency.

3.7 Power Supply (V⁺)

Positive power supply input voltage connection. It is recommended that a low ESR (equivalent series resistance) capacitor be used to bypass the power supply input to ground (GND).

4.0 DETAILED DESCRIPTION

4.1 Theory of Operation

The TC7660 charge pump converter inverts the voltage applied to the V^+ pin. The conversion consists of a two-phase operation (Figure 4-1). During the first phase, switches S_2 and S_4 are open and switches S_1 and S_3 are closed. C_1 charges to the voltage applied to the V^+ pin, with the load current being supplied from C_2 . During the second phase, switches S_2 and S_4 are closed and switches S_1 and S_3 are open. Charge is transferred from C_1 to C_2 , with the load current being supplied from C_1 .

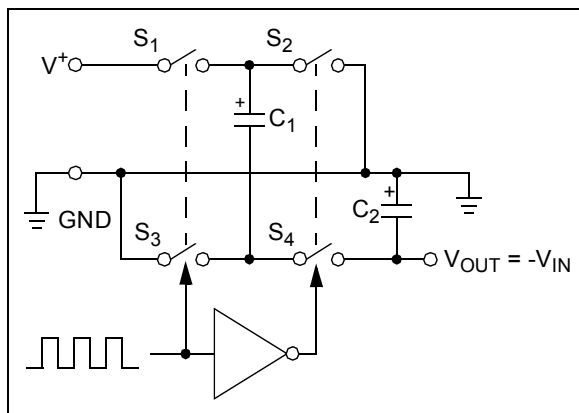


FIGURE 4-1: Ideal Switched Capacitor Inverter.

In this manner, the TC7660 performs a voltage inversion, but does not provide regulation. The average output voltage will drop in a linear manner with respect to load current. The equivalent circuit of the charge pump inverter can be modeled as an ideal voltage source in series with a resistor, as shown in Figure 4-2.

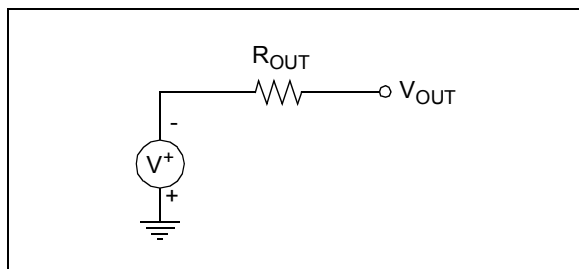


FIGURE 4-2: Switched Capacitor Inverter Equivalent Circuit Model.

The value of the series resistor (R_{OUT}) is a function of the switching frequency, capacitance and equivalent series resistance (ESR) of C_1 and C_2 and the on-resistance of switches S_1 , S_2 , S_3 and S_4 . A close approximation for R_{OUT} is given in the following equation:

EQUATION

$$R_{OUT} = \left[\frac{1}{f_{PUMP} \times C1} + 8R_{SW} + 4ESR_{C1} + ESR_{C2} \right]$$

Where:

$$f_{PUMP} = \frac{f_{OSC}}{2}$$

R_{SW} = on-resistance of the switches

ESR_{C1} = equivalent series resistance of C_1

ESR_{C2} = equivalent series resistance of C_2

4.2 Switched Capacitor Inverter Power Losses

The overall power loss of a switched capacitor inverter is affected by four factors:

1. Losses from power consumed by the internal oscillator, switch drive, etc. These losses will vary with input voltage, temperature and oscillator frequency.
2. Conduction losses in the non-ideal switches.
3. Losses due to the non-ideal nature of the external capacitors.
4. Losses that occur during charge transfer from C_1 to C_2 when a voltage difference between the capacitors exists.

Figure 4-3 depicts the non-ideal elements associated with the switched capacitor inverter power loss.

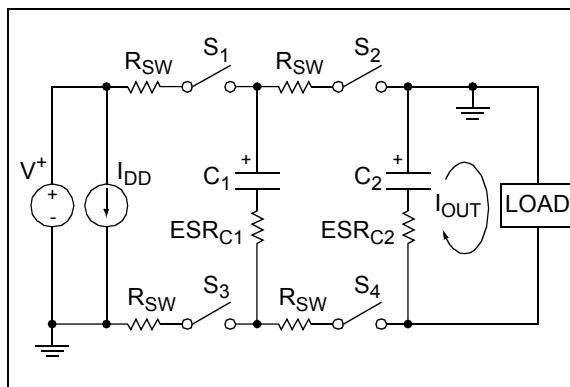


FIGURE 4-3: Non-Ideal Switched Capacitor Inverter.

The power loss is calculated using the following equation:

EQUATION

$$P_{LOSS} = I_{OUT}^2 \times R_{OUT} + I_{DD} \times V^+$$

5.0 APPLICATIONS INFORMATION

5.1 Simple Negative Voltage Converter

Figure 5-1 shows typical connections to provide a negative supply where a positive supply is available. A similar scheme may be employed for supply voltages anywhere in the operating range of +1.5V to +10V, keeping in mind that pin 6 (LV) is tied to the supply negative (GND) only for supply voltages below 3.5V.

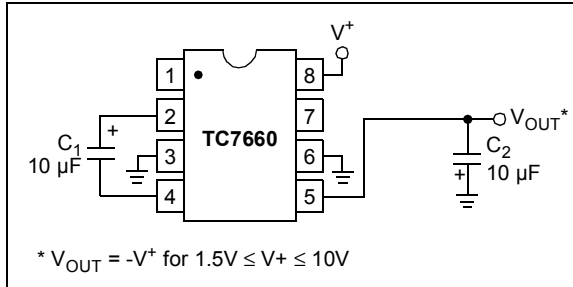


FIGURE 5-1: Simple Negative Converter.

The output characteristics of the circuit in Figure 5-1 are those of a nearly ideal voltage source in series with a 70Ω resistor. Thus, for a load current of -10 mA and a supply voltage of +5V, the output voltage would be -4.3V.

5.2 Paralleling Devices

To reduce the value of R_{OUT} , multiple TC7660 voltage converters can be connected in parallel (Figure 5-2). The output resistance will be reduced by approximately a factor of n , where n is the number of devices connected in parallel.

EQUATION

$$R_{OUT} = \frac{R_{OUT}(\text{of TC7660})}{n(\text{number of devices})}$$

While each device requires its own pump capacitor (C_1), all devices may share one reservoir capacitor (C_2). To preserve ripple performance, the value of C_2 should be scaled according to the number of devices connected in parallel.

5.3 Cascading Devices

A larger negative multiplication of the initial supply voltage can be obtained by cascading multiple TC7660 devices. The output voltage and the output resistance will both increase by approximately a factor of n , where n is the number of devices cascaded.

EQUATION

$$V_{OUT} = -n(V^+)$$

$$R_{OUT} = n \times R_{OUT}(\text{of TC7660})$$

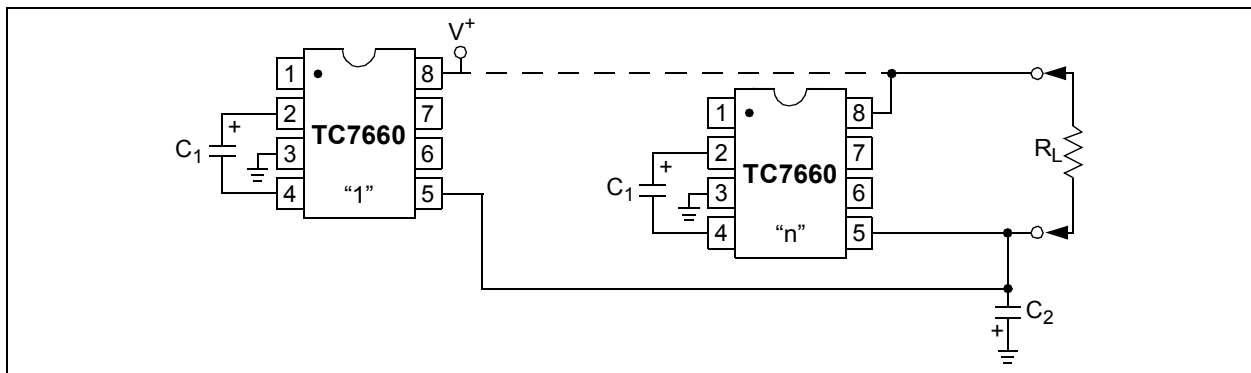


FIGURE 5-2: Paralleling Devices Lowers Output Impedance.

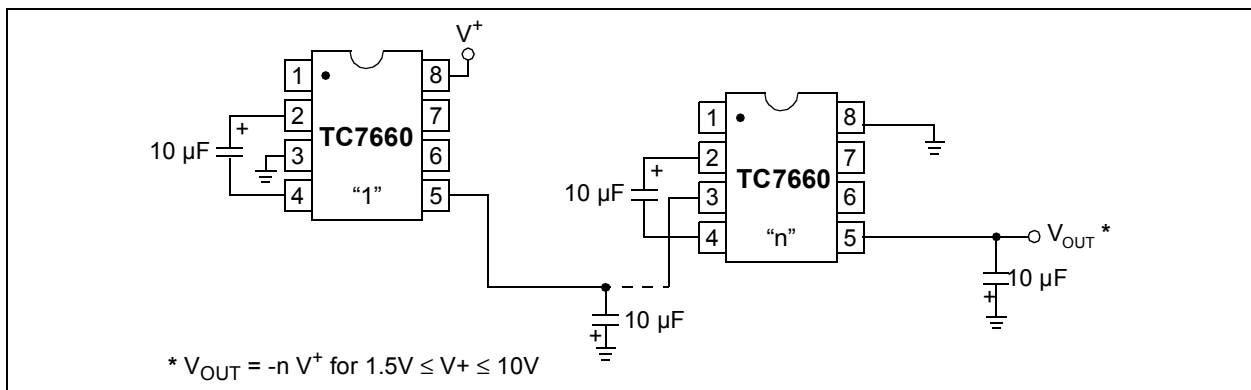


FIGURE 5-3: Increased Output Voltage By Cascading Devices.

5.4 Changing the TC7660 Oscillator Frequency

The operating frequency of the TC7660 can be changed in order to optimize the system performance. The frequency can be increased by over-driving the OSC input (Figure 5-4). Any CMOS logic gate can be utilized in conjunction with a 1 kΩ series resistor. The resistor is required to prevent device latch-up. While TTL level signals can be utilized, an additional 10 kΩ pull-up resistor to V^+ is required. Transitions occur on the rising edge of the clock input. The resultant output voltage ripple frequency is one half the clock input. Higher clock frequencies allow for the use of smaller pump and reservoir capacitors for a given output voltage ripple and droop. Additionally, this allows the TC7660 to be synchronized to an external clock, eliminating undesirable beat frequencies.

At light loads, lowering the oscillator frequency can increase the efficiency of the TC7660 (Figure 5-5). By lowering the oscillator frequency, the switching losses are reduced. Refer to Figure 2-3 to determine the typical operating frequency based on the value of the external capacitor. At lower operating frequencies, it may be necessary to increase the values of the pump and reservoir capacitors in order to maintain the desired output voltage ripple and output impedance.

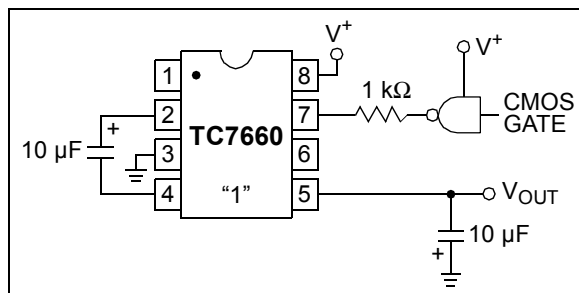


FIGURE 5-4: External Clocking.

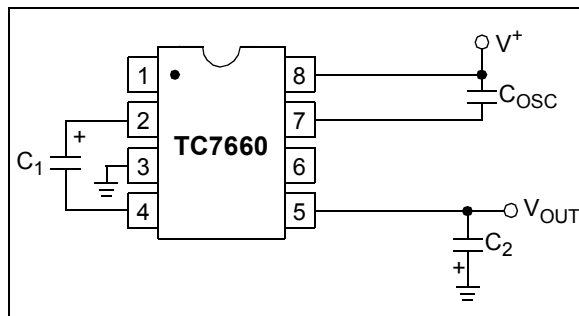


FIGURE 5-5: Lowering Oscillator Frequency.

5.5 Positive Voltage Multiplication

Positive voltage multiplication can be obtained by employing two external diodes (Figure 5-6). Refer to the theory of operation of the TC7660 (Section 4.1). During the half cycle when switch S_2 is closed, capacitor C_1 of Figure 5-6 is charged up to a voltage of $V^+ - V_{F1}$, where V_{F1} is the forward voltage drop of diode D_1 . During the next half cycle, switch S_1 is closed, shifting the reference of capacitor C_1 from GND to V^+ . The energy in capacitor C_1 is transferred to capacitor C_2 through diode D_2 , producing an output voltage of approximately:

EQUATION

$$V_{OUT} = 2 \times V^+ - (V_{F1} + V_{F2})$$

where:

V_{F1} is the forward voltage drop of diode D_1

and

V_{F2} is the forward voltage drop of diode D_2 .

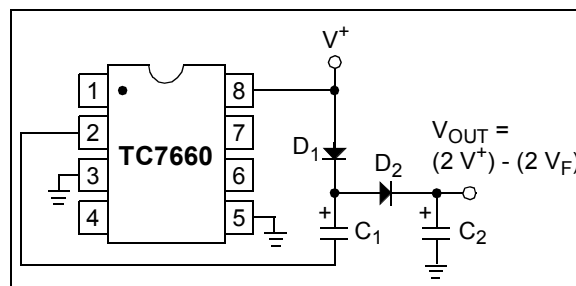


FIGURE 5-6: Positive Voltage Multiplier.

5.6 Combined Negative Voltage Conversion and Positive Supply Multiplication

Simultaneous voltage inversion and positive voltage multiplication can be obtained (Figure 5-7). Capacitors C_1 and C_3 perform the voltage inversion, while capacitors C_2 and C_4 , plus the two diodes, perform the positive voltage multiplication. Capacitors C_1 and C_2 are the pump capacitors, while capacitors C_3 and C_4 are the reservoir capacitors for their respective functions. Both functions utilize the same switches of the TC7660. As a result, if either output is loaded, both outputs will drop towards GND.

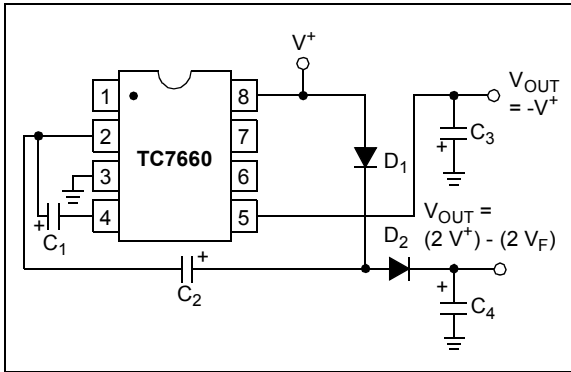


FIGURE 5-7: Combined Negative Converter And Positive Multiplier.

5.7 Efficient Positive Voltage Multiplication/Conversion

Since the switches that allow the charge pumping operation are bidirectional, the charge transfer can be performed backwards as easily as forwards. Figure 5-8 shows a TC7660 transforming -5V to +5V (or +5V to +10V, etc.). The only problem here is that the internal clock and switch-drive section will not operate until some positive voltage has been generated. An initial inefficient pump, as shown in Figure 5-7, could be used to start this circuit up, after which it will bypass the other (D_1 and D_2 in Figure 5-7 would never turn on), or else the diode and resistor shown dotted in Figure 5-8 can be used to "force" the internal regulator on.

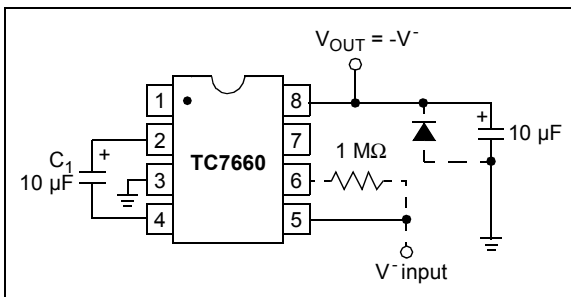
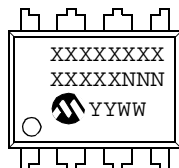


FIGURE 5-8: Positive Voltage Conversion.

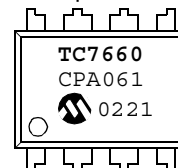
6.0 PACKAGING INFORMATION

6.1 Package Marking Information

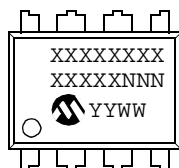
8-Lead PDIP (300 mil)



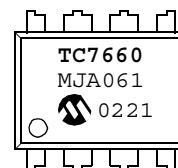
Example:



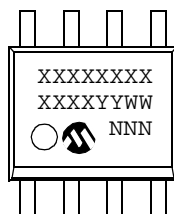
8-Lead Cerdip (300 mil)



Example:



8-Lead SOIC (150 mil)



Example:

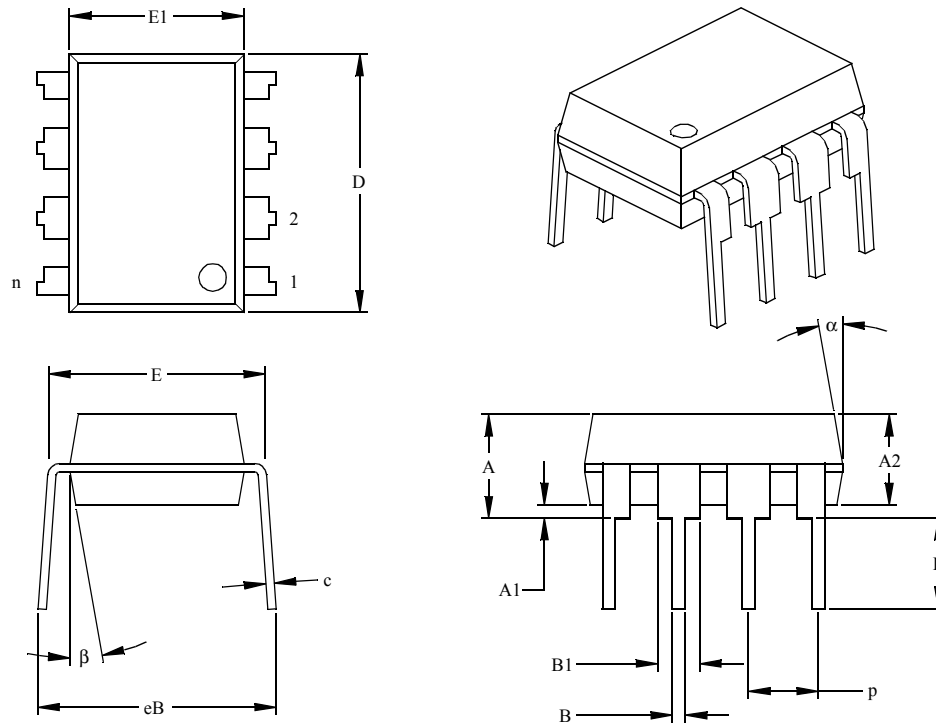


Legend:	XX...X	Customer specific information*
	YY	Year code (last 2 digits of calendar year)
	WW	Week code (week of January 1 is week '01')
	NNN	Alphanumeric traceability code

Note: In the event the full Microchip part number cannot be marked on one line, it will be carried over to the next line thus limiting the number of available characters for customer specific information.

* Standard marking consists of Microchip part number, year code, week code, traceability code (facility code, mask rev#, and assembly code). For marking beyond this, certain price adders apply. Please check with your Microchip Sales Office.

8-Lead Plastic Dual In-line (P) – 300 mil (PDIP)



Units		INCHES*			MILLIMETERS		
Dimension Limits		MIN	NOM	MAX	MIN	NOM	MAX
Number of Pins	n		8			8	
Pitch	p		.100			2.54	
Top to Seating Plane	A	.140	.155	.170	3.56	3.94	4.32
Molded Package Thickness	A2	.115	.130	.145	2.92	3.30	3.68
Base to Seating Plane	A1	.015			0.38		
Shoulder to Shoulder Width	E	.300	.313	.325	7.62	7.94	8.26
Molded Package Width	E1	.240	.250	.260	6.10	6.35	6.60
Overall Length	D	.360	.373	.385	9.14	9.46	9.78
Tip to Seating Plane	L	.125	.130	.135	3.18	3.30	3.43
Lead Thickness	c	.008	.012	.015	0.20	0.29	0.38
Upper Lead Width	B1	.045	.058	.070	1.14	1.46	1.78
Lower Lead Width	B	.014	.018	.022	0.36	0.46	0.56
Overall Row Spacing	§ eB	.310	.370	.430	7.87	9.40	10.92
Mold Draft Angle Top	α	5	10	15	5	10	15
Mold Draft Angle Bottom	β	5	10	15	5	10	15

* Controlling Parameter

§ Significant Characteristic

Notes:

Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed .010" (0.254mm) per side.

JEDEC Equivalent: MS-001

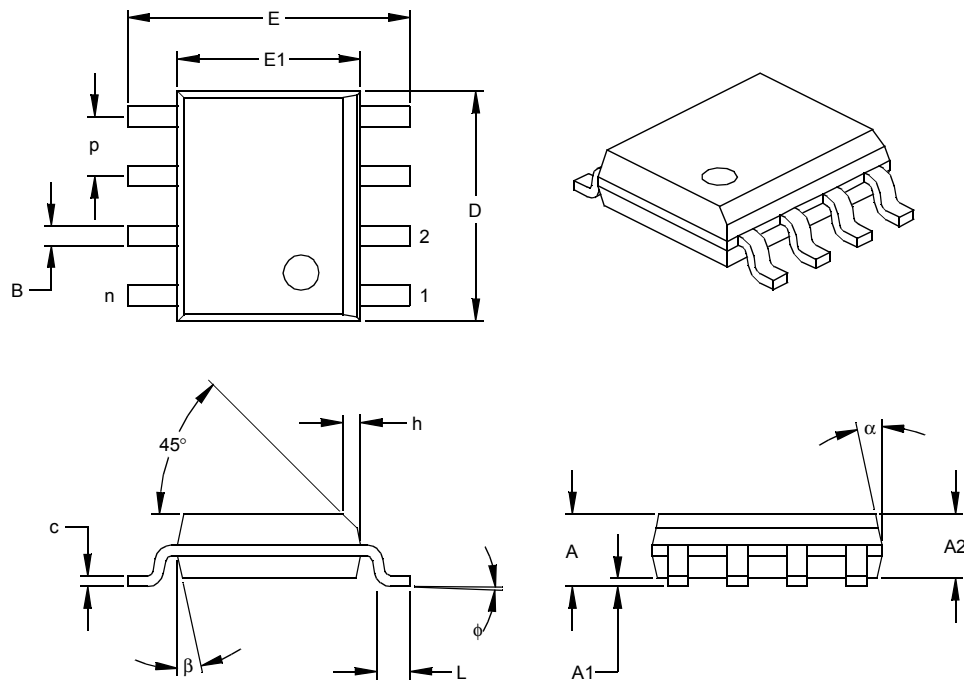
Drawing No. C04-018

TC7660

8-Lead Ceramic Dual In-line – 300 mil (CERDIP)

Packaging diagram not available at this time.

8-Lead Plastic Small Outline (SN) – Narrow, 150 mil (SOIC)



Units		INCHES*			MILLIMETERS		
Dimension Limits		MIN	NOM	MAX	MIN	NOM	MAX
Number of Pins	n		8			8	
Pitch	p		.050			1.27	
Overall Height	A	.053	.061	.069	1.35	1.55	1.75
Molded Package Thickness	A2	.052	.056	.061	1.32	1.42	1.55
Standoff §	A1	.004	.007	.010	0.10	0.18	0.25
Overall Width	E	.228	.237	.244	5.79	6.02	6.20
Molded Package Width	E1	.146	.154	.157	3.71	3.91	3.99
Overall Length	D	.189	.193	.197	4.80	4.90	5.00
Chamfer Distance	h	.010	.015	.020	0.25	0.38	0.51
Foot Length	L	.019	.025	.030	0.48	0.62	0.76
Foot Angle	φ	0	4	8	0	4	8
Lead Thickness	c	.008	.009	.010	0.20	0.23	0.25
Lead Width	B	.013	.017	.020	0.33	0.42	0.51
Mold Draft Angle Top	α	0	12	15	0	12	15
Mold Draft Angle Bottom	β	0	12	15	0	12	15

* Controlling Parameter
§ Significant Characteristic

Notes:
Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed .010" (0.254mm) per side.
JEDEC Equivalent: MS-012
Drawing No. C04-057

TC7660

NOTES:

PRODUCT IDENTIFICATION SYSTEM

To order or obtain information, e.g., on pricing or delivery, refer to the factory or the listed sales office.

<u>PART NO.</u>	<u>X</u>	<u>/XX</u>
Device	Temperature Range	Package
Device: TC7660: DC-to-DC Voltage Converter		
Temperature Range:	C = 0°C to +70°C E = -40°C to +85°C I = -25°C to +85°C (CERDIP only) M = -55°C to +125°C (CERDIP only)	
Package:		PA = Plastic DIP, (300 mil body), 8-lead JA = Ceramic DIP, (300 mil body), 8-lead OA = SOIC (Narrow), 8-lead OA713 = SOIC (Narrow), 8-lead (Tape and Reel)

Examples:

- a) TC7660COA: Commercial Temp., SOIC package.
- b) TC7660COA713: Tape and Reel, Commercial Temp., SOIC package.
- c) TC7660CPA: Commercial Temp., PDIP package.
- d) TC7660EOA: Extended Temp., SOIC package.
- e) TC7660EOA713: Tape and Reel, Extended Temp., SOIC package.
- f) TC7660EPA: Extended Temp., PDIP package.
- g) TC7660IJA: Industrial Temp., CERDIP package
- h) TC7660MJA: Military Temp., CERDIP package.

Sales and Support

Data Sheets

Products supported by a preliminary Data Sheet may have an errata sheet describing minor operational differences and recommended workarounds. To determine if an errata sheet exists for a particular device, please contact one of the following:

1. Your local Microchip sales office
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Please specify which device, revision of silicon and Data Sheet (include Literature #) you are using.

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TC7660

NOTES:

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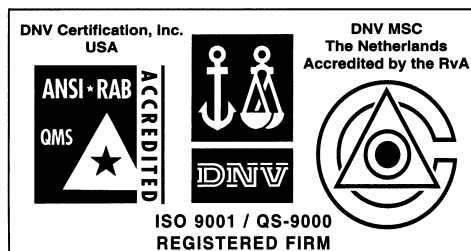
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11/15/02